

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	39	ravi near kramadhati.in.	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 7 15:03	
2	BRS	L2	243	(stress\$3 near10 channel) near25 (substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 7 15:04	
3	BRS	L3	44	(stress\$3 near10 channel) near25 (transistor\$1) near25 (substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 7 15:12	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	18305	(channel) near25 (transistor\$1) near25 (substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/27 15:12	
5	BRS	L5	219	(channel) near25 (transistor\$1) near25 (manufactur\$3 near5 substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/27 15:12	
6	BRS	L6	202	(channel) near15 (transistor\$1) near25 (manufactur\$3 near5 substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/27 15:21	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L7	3	(channel near25 (strain\$2 or stress\$3)) near15 (transistor\$1) near25 (manufactur\$3 near5 substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 7 15:34	
8	BRS	L8	150	(channel near25 (strain\$2 or stress\$3)) near15 (transistor\$1) near25 (substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 7 15:51	
9	BRS	L9	2017	(substrate) near25 (cte)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 7 15:52	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	53	(intermediate or handle) near25 (substrate) near25 (cte)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/27 15:52	
11	BRS	L11	53	((intermediate or handle)) near25 ((substrate) near25 (cte))	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/27 16:01	
12	BRS	L12	3	((intermediate or handle)) near25 ((substrate) near25 (cte)) near29 (diamond)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/27 16:03	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	3	((intermediate or handle)) near25 ((substrate) near25 (cte)) near29 ((diamond))	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/27 16:04	
14	BRS	L14	0	((intermediate or handle)) near25 ((substrate) near25 (cte)) near29 ((coll\$3))	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/27 16:04	
15	BRS	L15	0	((intermediate or handle)) near25 ((substrate) near25 (cte)) near29 ((cool\$3))	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/27 16:04	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
16	BRS	L16	2	((intermediate or handle)) near25 (cte) near29 ((cool\$3))	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/27 16:05	
17	BRS	L17	75	((intermediate or handle or substrate)) near25 (cte) near29 ((cool\$3))	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/27 16:21	
18	BRS	L18	2	((intermediate or handle or substrate)) near25 (cte) near29 ((cool\$3)) near25 (remov\$3)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/27 16:13	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
19	BRS	L19	0	singulating near10 substrate near15 channel	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 7 16:22	
20	BRS	L20	8	singulat\$3 near10 substrate near15 channel	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 7 16:24	
21	BRS	L22	1	(sigulat\$3 or cutt\$3) near15 (stress or strain\$2) near10 (substrate near15 channel)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 7 16:30	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
22	BRS	L23	2	(sigulat\$3 or cut\$3) near15 (stress or strain\$2) near10 (substrate near15 channel)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 7 16:25	
23	BRS	L21	488	(stress or strain\$2) near10 (substrate near15 channel)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 7 16:26	

	U	1	Document ID	Title	Current OR	Pages
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20020017642 A1	Semiconductor substrate, field effect transistor, method of forming SiGe layer and method of forming strained Si layer using same, and method of manufacturing field effect transistor	257/19	15
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6525338 B2	Semiconductor substrate, field effect transistor, method of forming SiGe layer and method of forming strained Si layer using same, and method of manufacturing field effect transistor	257/19	14
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020017642 A	Semiconductor substrate for field effect transistor, comprises silicon substrate having laminated layers of silicon-germanium buffer layer comprising gradually increasing germanium composition ratio		14